UNR92A1G

Silicon NPN epitaxial planar type

For digital circuits

■ Features

- Optimum for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	50	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Collector current	I_{C}	80	mA	
Total power dissipation	P_{T}	125	mW	
Junction temperature	T _j	125	°C	
Storage temperature	T _{stg}	-55 to +125	Sicol	

Package

- Code
- SSMini3-F3
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

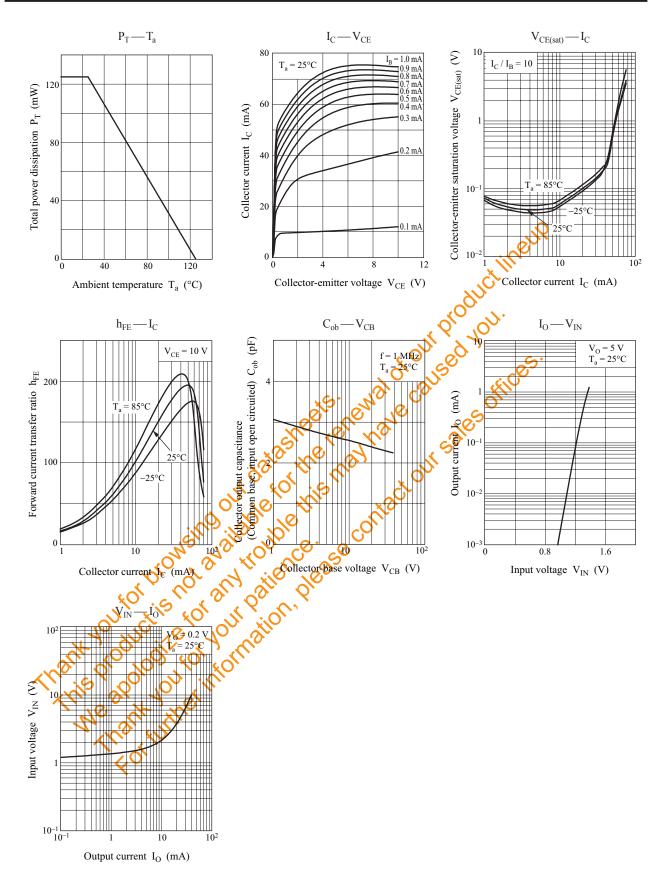
■ Marking Symbol: FK



Absolute Maximum Ratings T _a							
Parameter	Symbol	Rating	Rating Unit 3: Collector				
Collector-base voltage (Emitter open)	V _{CBO}	50	V	arking Syr	nhol: Ek	•	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	alking Syl	ilibol. Fr	•	
Collector current	I_{C}	80	mA Int	ernal Con	nection		
Total power dissipation	P_{T}	125	mW C	SO	R _b S	. ✓ ° C	
Junction temperature	T _j	125	°C 00. 2013	B⊶	W I		
Storage temperature	T _{stg}	-55 to +125	S.C. NO.	(0)	$R_2 \ge$	• E	
■ Electrical Characteristics T _a =2	availa,	inello proportion of the propo	V mA mW °C NOTACE CONTROL CON				
Parameter	Symb	39 7.6	Conditions	Min	Тур	Max	
Collector-base voltage (Emitter open)	V _{CBO}	$C = 10 \mu$	$A, I_E = 0$	50			Unit
Collector-emitter voltage (Base open)	V	7					Unit V
		$I_C = 2 \text{ mA}$	$I_{B} = 0$	50			
Collector-base cutoff current Emitter open	,, 	$I_C = 2 \text{ mA}$	$_{-}, I_{B} = 0$	50		0.1	V
Collector-base cutoff current (Base on Collector-emitter cutoff current (Base on	en) (G _{CBO}	$I_C = 2 \text{ mA}$	$I_{B} = 0$ $V, I_{E} = 0$	50		0.1	V V
	en) I_{CEO}	$I_C = 2 \text{ mA}$ $V_{CB} = 50$	$V, I_{B} = 0$ $V, I_{E} = 0$ $V, I_{B} = 0$	50			V V μA
Collector-emitter cutoff current (Base on	en) I_{CEO}	$I_{C} = 2 \text{ mA}$ $V_{CB} = 50^{\circ}$ $V_{CE} = 50^{\circ}$ $V_{EB} = 6 \text{ V}$	$V, I_{B} = 0$ $V, I_{E} = 0$ $V, I_{B} = 0$	35		0.5	V V μΑ μΑ
Collector-emitter cutoff current (Base on Emitter-base cutoff current (Collector open	en) I_{CEO} en) I_{EBO}	$I_C = 2 \text{ mA}$ $V_{CB} = 50$ $V_{CE} = 50$ $V_{EB} = 6 \text{ V}$ $V_{CE} = 10$	$V, I_B = 0$ $V, I_E = 0$ $V, I_B = 0$ $V, I_C = 0$	50		0.5	V V μΑ μΑ
Collector-emitter cutoff current (Base on Emitter-base cutoff current (Collector operation) Forward current transfer ratio	en) I_{CEO} en) I_{EBO} h_{FE}	$I_{C} = 2 \text{ mA}$ $V_{CB} = 50$ $V_{CE} = 50$ $V_{EB} = 6 \text{ V}$ $V_{CE} = 10$ $I_{C} = 10 \text{ ma}$	$V, I_B = 0$ $V, I_E = 0$ $V, I_B = 0$ $V, I_C = 0$ $V, I_C = 5 \text{ mA}$	50		0.5	V V μA μA mA
Collector-emitter cutoff current (Base on Emitter-base cutoff current (Collector operation) Forward current transfer ratio Collector-emitter saturation Voltage	en) I_{CBO} en) I_{CEO} en) I_{EBO} h_{FE} $V_{CE(sa)}$	$I_{C} = 2 \text{ mA}$ $V_{CB} = 50^{\circ}$ $V_{CE} = 50^{\circ}$ $V_{EB} = 6 \text{ V}$ $V_{CE} = 10^{\circ}$ $I_{C} = 10 \text{ mA}$ $V_{CC} = 5 \text{ V}$	$I_{A}I_{B} = 0$ $I_{A}I_{B} = 0$ $I_{A}I_{C} = 0$ I_{A	35		0.5	V V μA μA mA
Collector-emitter cutoff current (Base on Emitter-base cutoff current (Collector operation) Forward current transfer ratio Collector-emitter saturation voltage Output voltage high-level	$\begin{array}{c} \text{en)} \text{Q_{CBO}} \\ \text{en)} \text{I_{CEO}} \\ \text{en)} \text{I_{EBO}} \\ \text{h_{FE}} \\ \text{$V_{\text{CE}(sa)}$} \\ \text{V_{OH}} \end{array}$	$I_{C} = 2 \text{ mA}$ $V_{CB} = 50^{\circ}$ $V_{CE} = 50^{\circ}$ $V_{EB} = 6 \text{ V}$ $V_{CE} = 10^{\circ}$ $I_{C} = 10 \text{ mA}$ $V_{CC} = 5 \text{ V}$	$V, I_{B} = 0$ $V, I_{E} = 0$ $V, I_{C} = 0$ $V, I_{C} = 0$ $V, I_{C} = 5 \text{ mA}$ $A, I_{B} = 0.3 \text{ mA}$ $V, V_{B} = 0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$	35	10	0.5 0.5 0.25	V V μA μA mA V
Collector-emitter cutoff current (Collector open Emitter-base cutoff current (Collector open Forward current transfer ratio Collector-emitter saturation Collage Output voltage high-level Output voltage low-level	$\begin{array}{c} \text{en)} \text{Q_{CBO}} \\ \text{I}_{\text{CEO}} \\ \text{en)} \text{I}_{\text{EBO}} \\ \text{h_{FE}} \\ \text{$V_{\text{CE(sa)}}$} \\ \text{V_{OH}} \\ \end{array}$	$I_{C} = 2 \text{ mA}$ $V_{CB} = 50^{\circ}$ $V_{EB} = 6 \text{ V}$ $V_{CE} = 10^{\circ}$ $I_{C} = 10 \text{ m}$ $V_{CC} = 5 \text{ V}$	$V, I_{B} = 0$ $V, I_{E} = 0$ $V, I_{C} = 0$ $V, I_{C} = 0$ $V, I_{C} = 5 \text{ mA}$ $A, I_{B} = 0.3 \text{ mA}$ $V, V_{B} = 0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$	35	10 1.0	0.5 0.5 0.25	V V μA μA mA V V

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

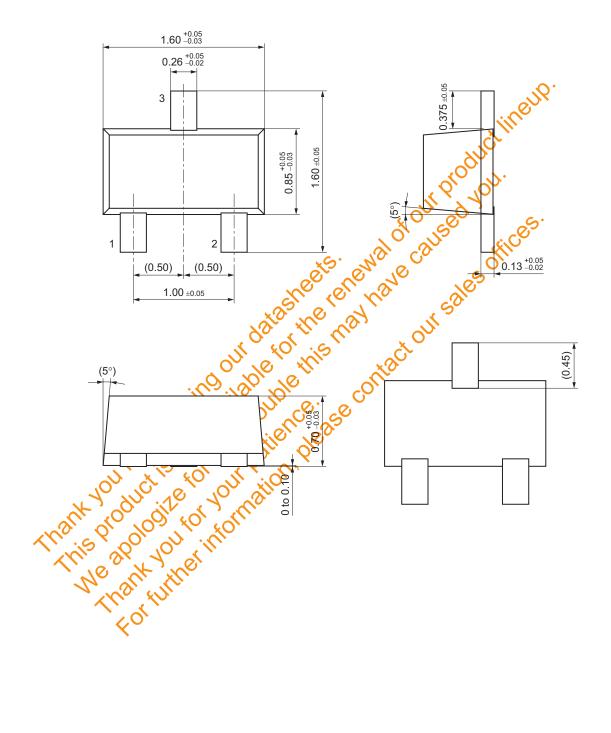
UNR92A1G Panasonic



2 SJH00243AED

Panasonic UNR92A1G

SSMini3-F3 Unit: mm



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